

Page i

INTEGRATED CIRCUITS, SILICON MONOLITHIC,
BIPOLAR, ADVANCED LOW POWER SCHOTTKY,
3-LINE TO 8-LINE DECODERS/DEMULTIPLEXERS,
BASED ON TYPE 54ALS138

ESCC Detail Specification No. 9205/012

# ISSUE 1 October 2002





#### **ESCC Detail Specification**

PAGE	ii
ISSUE	1

#### **LEGAL DISCLAIMER AND COPYRIGHT**

European Space Agency, Copyright © 2002. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or allleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Ageny and provided that it is not used for a commercial purpose, may be:

- copied in whole in any medium without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



# european space agency agence spatiale européenne

Pages 1 to 28

INTEGRATED CIRCUITS, SILICON MONOLITHIC,
BIPOLAR, ADVANCED LOW POWER SCHOTTKY,
3-LINE TO 8-LINE DECODERS/DEMULTIPLEXERS,
BASED ON TYPE 54ALS138

ESA/SCC Detail Specification No. 9205/012



# space components coordination group

	Approved by					
Date	SCCG Chairman	ESA Director General or his Deputy				
January 1992	Pomomines	I late				
June 1994	Comment	tur let				
	January 1992	Date SCCG Chairman  January 1992				



Rev. 'A'

PAGE 2

ISSUE 2

## **DOCUMENTATION CHANGE NOTICE**

			<u> </u>
Rev. Letter	Rev. Date	CHANGE Reference Item	Approved DCR No.
		This Issue supersedes Issue 1 and incorporates all modifications defined in Revision 'A' to Issue 1 and the following DCR's:- Cover Page : Title corrected DCN Table 1(a) : Lead Material and/or Finish amended Figures 2 : Imperial dimensions and references deleted Figure 2(c) : In drawing, Note 6 corrected to "10" Notes to Figures : Title amended : Note 1, amended to read "Figure 2(b)" Figure 3(a) : Comparison Table added Figure 3(b) : Note 2 added Para. 4.2.2 : Deviation deleted, "None." added Para. 4.2.4 : Deviation deleted, "None" added Para. 4.2.5 : Deviation deleted, "None" added Para. 4.2.5 : Paragraph amended Para. 4.4.2 : Paragraph amended Para. 4.5.3 : "Type Variant, as applicable" amended to refer to Table 1(a) Para. 4.6.3 : Reference to functional test sequence deleted Para. 4.7.1 : Expanded to identify the stated temperature as Tamb Figure 4(f) : Note 2 added Para. 4.8 : Title expanded	23456 None 22881 22881 23456 22881 22881 23456 21048 22919 22919 22881 23455 23455 23455 23455 23456 23455
'A'	June '94	P1. Cover Page P2. DCN P14. Para. 4.3.2 : Weights amended	None None 221047



PAGE 3

ISSUE 2

## TABLE OF CONTENTS

1.	GENERAL	Page <b>5</b>
1.1 1.2 1.3	Scope Component Type Variants Maximum Ratings	5 5 5
1.4	Parameter Derating Information	5
1.5	Physical Dimensions	5
1.6	Pin Assignment	5
1.7	Truth Table	5
1.8	Circuit Schematic	5
1.9	Functional Diagram	5
2.	APPLICABLE DOCUMENTS	13
3.	TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS	13
4.	REQUIREMENTS	13
4.1	General	13
4.2	Deviations from Generic Specification	13
4.2.1	Deviations from Special In-process Controls	13
4.2.2	Deviations from Final Production Tests	13
4.2.3	Deviations from Burn-in Tests	13
4.2.4	Deviations from Qualification Tests	13
4.2.5	Deviations from Lot Acceptance Tests	14
4.3 4.3.1	Mechanical Requirements Dimension Check	14 14
4.3.1	Weight	14
4.4	Materials and Finishes	14
4.4.1	Case	14
4.4.2	Lead Material and Finish	14
4.5	Marking	14
4.5.1	General	14
4.5.2	Lead Identification	14
4.5.3	The SCC Component Number	16
4.5.4	Traceability Information	15
4.6	Electrical Measurements	15
4.6.1	Electrical Measurements at Room Temperature	15
4.6.2	Electrical Measurements at High and Low Temperatures	15
4.6.3	Circuits for Electrical Measurements	15
4.7	Burn-in Tests	15
4.7.1	Parameter Drift Values	15
4.7.2	Conditions for Power Burn-in	15
4.7.3	Electrical Circuits for Power Burn-in	15
4.8	Environmental and Endurance Tests	26
4.8.1 4.8.2	Electrical Measurements on Completion of Environmental Tests  Electrical Measurements at Intermediate Points during Endurance Tests	26 26
4.8.3	Electrical Measurements on Completion of Endurance Tests	26
4.8.4	Conditions for Operating Life Tests	26
4.8.5	Electrical Circuits for Operating Life Tests	26
4.8.6	Conditions for High Temperature Storage Test	26
	<u> </u>	



PAGE 4

ISSUE 2

TABLE	<u>ES</u>	<u>Page</u>
1(a) 1(b) 2 3 4 5 6	Type Variants Maximum Ratings Electrical Measurements at Room Temperature, d.c. Parameters Electrical Measurements at Room Temperature, a.c. Parameters Electrical Measurements at High and Low Temperatures Parameter Drift Values Conditions for Power Burn-in and Operating Life Test Electrical Measurements on Completion of Environmental Tests and at Intermediate Points and on Completion of Endurance Tests	6 6 16 18 19 24 24
FIGUE		
1 2 3(a) 3(b) 3(c) 3(d) 4 5	Not applicable Physical Dimensions Pin Assignment Truth Table Circuit Schematic Functional Diagram Circuits for Electrical Measurements Electrical Circuit for Power Burn-in and Operating Life Test  NDICES (Applicable to specific Manufacturers only)	7 11 11 12 12 21 25
'Α'	Agreed Deviations for Texas Instruments (F)	28



PAGE

ISSUE 2

5

#### 1. **GENERAL**

#### 1.1 SCOPE

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon monolithic, bipolar, advanced low power Schottky, 3-Line to 8-Line Decoder/Demultiplexer, based on Type 54ALS138. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000, the requirements of which are supplemented herein.

#### 1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification, are given in Table 1(a).

#### 1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

#### 1.4 PARAMETER DERATING INFORMATION (FIGURE 1)

Not applicable.

#### 1.5 PHYSICAL DIMENSIONS

The physical dimensions of the integrated circuits specified herein are shown in Figure 2.

#### 1.6 PIN ASSIGNMENT

As per Figure 3(a).

#### 1.7 TRUTH TABLE

As per Figure 3(b).

#### 1.8 <u>CIRCUIT SCHEMATIC</u>

As per Figure 3(c).

#### 1.9 FUNCTIONAL DIAGRAM

As per Figure 3(d).



PAGE 6

ISSUE 2

#### **TABLE 1(a) - TYPE VARIANTS**

VARIANT	CASE	FIGURE	LEAD MATERIAL AND/OR FINISH
01	FLAT	2(a)	D7
02	FLAT	2(a)	G4
03	CCP	2(b)	7
04	CCP	2(b)	4
05	DIL	2(c)	D7
06	DIL	2(c)	G4

#### **TABLE 1(b) - MAXIMUM RATINGS**

NO.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	Supply Voltage	V <sub>CC</sub>	- 0.5 to 7.0	V	-
2	Input Voltage	V <sub>IN</sub>	- 0.5 to 7.0	٧	Note 1
3	Device Dissipation	$P_{D}$	55	mWdc	Note 2
4	Operating Temperature Range	T <sub>op</sub>	– 55 to + 125	°C	-
5	Storage Temperature Range	T <sub>stg</sub>	- 65 to + 150	°C	-
6	Soldering Temperature For FP and DIP For CCP	T <sub>sol</sub>	+ 265 + 245	°C	Note 3 Note 4

#### NOTES

- 1. Input Current limited to 18mA.
- 2. Must withstand added  $P_D$  due to short circuit conditions (i.e.  $I_{OS}$ ) at 1 output for 5 seconds.
- 3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the package and the same lead shall not be resoldered until 3 minutes have elapsed.
- 4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

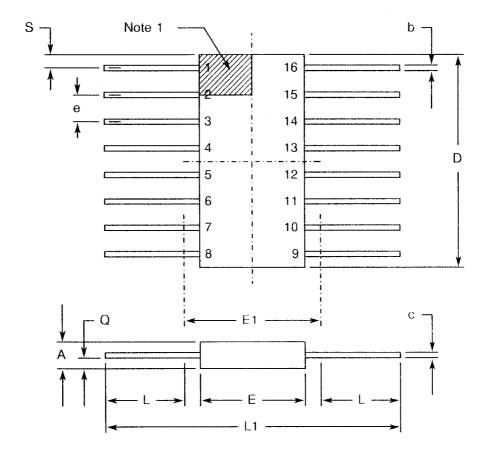


PAGE 7

ISSUE 2

#### FIGURE 2 - PHYSICAL DIMENSIONS

#### FIGURE 2(a) - FLAT PACKAGE



SYMBOL	MILLIM	NOTES		
STINIBUL	MIN	MAX	NOTES	
А	1.24	2.03		
b	0.38	0.48	8	
С	0.08	0.15	8	
D	D 9.65 11.02			
E	6.10	6.60		
E1	-	7.11	4	
е	1.27 T	5, 9		
L	6.35	9.40		
L1	.1 19.05 -			
Q	0.25	0.89	2	
S	0.25	0.76	7	



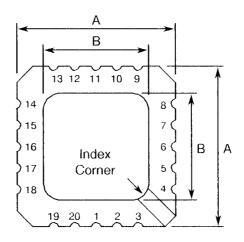
PAGE

ISSUE 2

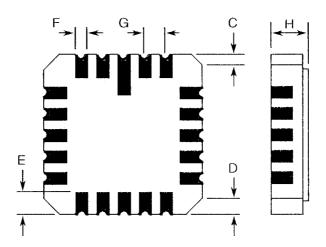
8

## FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

#### FIGURE 2(b) - SQUARE CHIP CARRIER PACKAGE (3 LAYER BASE)



20 Terminal



SYMBOL	MILLIM	NOTES		
STWBOL	MIN	MAX	NOTES	
А	8.687	9.093		
В	7.798	9.093		
С	C 0.250 0.510			
D	0.889	1.143	12	
E	E 1.140 1.400			
F.	F 0.559		8	
G	1.27 T`	5, 9		
Н	1.630	2.540		



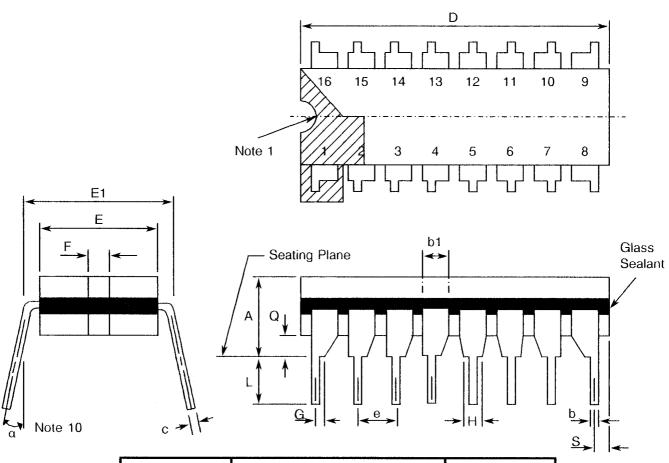
PAGE

9

ISSUE 2

## FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

#### FIGURE 2(c) - DUAL-IN-LINE PACKAGE



SYMBOL	MILLIM	NOTES	
STIVIBOL	MIN	MAX	NOTES
Α	-	5.08	
b	0.38	0.58	8
b1	<b>.</b>	1.78	8
С	0.203	0.356	8
D	19.18	19.94	
E	6.22	7.11	
E1	<b>E1</b> 7.37 7.87		4
е	2.54 TY	/PICAL	6, 9
G	0.305	-	13
Н	0.76	-	14
L	3.30	5.08	
Q ·	0.51	2.03	3
S	0.38	1.27	7
α	0°	15°	10



PAGE 10

ISSUE 2

#### FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

#### NOTES TO FIGURES 2(a) TO 2(c) INCLUSIVE

- 1. Index area; a notch or dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages the index shall be as defined in Figure 2(b).
- 2. Dimension Q shall be measured at the point of exit of the lead from the body.
- 3. Dimension Q shall be measured from the seating plane to the base plane.
- 4. This dimension allows for off-centre lids, meniscus and glass overrun.
- 5. The true position pin or terminal spacing is 1.27mm between centrelines. Each pin or terminal centreline shall be located within ±0.13mm of its true longitudinal position relative to Pins 1 and the highest pin number.
- 6. The true position pin spacing is 2.54mm between centrelines. Each pin centreline shall be located within ± 0.25mm of its true longitudinal position relative to Pins 1 and the highest pin number.
- 7. Applies to all 4 corners.
- 8. All leads or terminals.
- 14 spaces for flat and dual-in-line packages.
   16 spaces for chip carrier packages.
- 10. Lead centre when  $\alpha$  is 0°.
- 11. Index corner only 2 dimensions.
- 12. 3 non-index corners 6 dimensions.
- 13. 4 Terminals.
- 14. 12 Terminals.

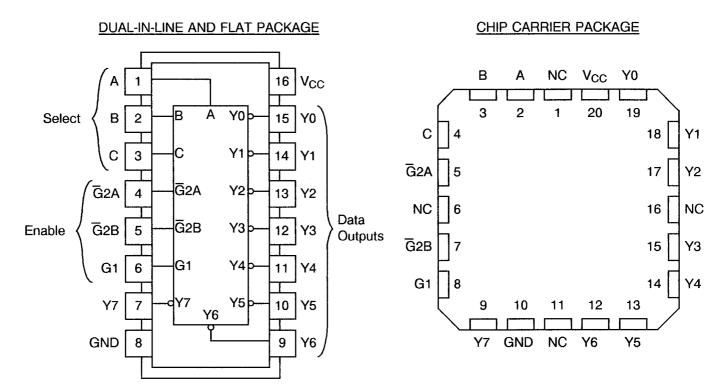


PAGE 11

ISSUE 2

**TOP VIEW** 

#### FIGURE 3(a) - PIN ASSIGNMENT



#### FLAT PACKAGE AND DUAL-IN-LINE TO CHIP CARRIER PIN ASSIGNMENT

**TOP VIEW** 

FLAT PACKAGE AND

**DUAL-IN-LINE PIN OUTS** 9 2 3 10 11 12 13 14 15 16 CHIP CARRIER PIN OUTS 2 3 9 10 12 13 14 15 18 19 20 17

#### FIGURE 3(b) - TRUTH TABLE

	INPUTS					OUTDUTS						
EN	ENABLE		SELECT		OUTPUTS							
G1	G2 (1)	С	В	Α	Y0	Y1	Y2	<b>Y</b> 3	Y4	Y5	Y6	Y7
X	Н	Χ	Х	Χ	Н	Н	Н	Н	Н	Н	Н	Н
L	Х	Х	X	Χ	Н	Н	Н	Н	Н	Н	Н	н
Н	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н
Н	L	L	L	Н	Н	L	Н	Н	Н	Н	Н	н
Н	L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н
Н	L	L	Н	Н	Н	Н	Н	L	Н	Н	Н	н
Н	L	Н	L	L	Н	Н	Н	Н	L	Н	Н	н
Н	L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	н
Н	L	Н	Н	L	н	H	Н	Н	Н	Н	L	Н
Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L

#### **NOTES**

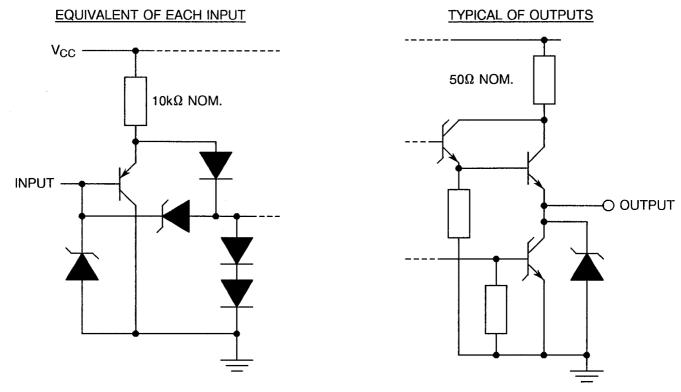
- 1.  $\overline{G}2 = \overline{G}2A + \overline{G}2B$
- 2. Logic Level Definitions: L = Low Level, H = High Level, X = Irrelevant.



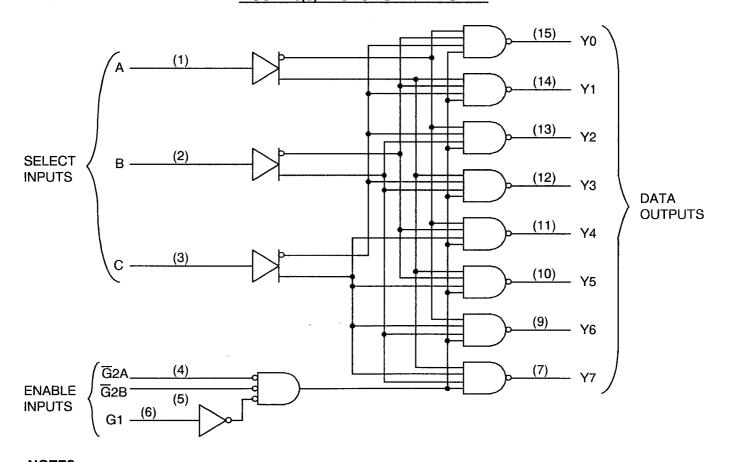
PAGE 12

ISSUE 2

#### FIGURE 3(c) - CIRCUIT SCHEMATIC



#### FIGURE 3(d) - FUNCTIONAL DIAGRAM



### **NOTES**

1. Pin numbers shown are for flat and dual-in-line packages; for chip carrier pins, see Figure 3(a).



PAGE 13

ISSUE 2

#### 2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.
- (b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

#### 3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviation is used:-

I<sub>OS/2</sub> - One half of the true output short circuit current.

#### 4. REQUIREMENTS

#### 4.1 GENERAL

The complete requirements for procurement of the integrated circuits specified herein shall be as stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

#### 4.2 DEVIATIONS FROM GENERIC SPECIFICATION

#### 4.2.1 Deviations from Special In-process Controls

None.

#### 4.2.2 Deviations from Final Production Tests (Chart II)

None.

#### 4.2.3 <u>Deviations from Burn-in Tests (Chart III)</u>

- (a) Para. 7.1.1(a), "High Temperature Reverse Bias" tests and subsequent electrical measurements related to this test shall be omitted.
- (b) Para. 9.9.2, "Electrical Measurements at High and Low Temperatures": Only a test result summary, based on go-no-go tests and presented in histogram form is required.

#### 4.2.4 <u>Deviations from Qualification Tests (Chart IV)</u>

None.



Rev. 'A'

PAGE 14

ISSUE 2

#### 4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

#### 4.3 MECHANICAL REQUIREMENTS

#### 4.3.1 <u>Dimension Check</u>

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

#### 4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be 0.7 grammes for the flat package, 0.6 grammes for the chip carrier package and 2.2 grammes for the dual-in-line package.

#### 4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

#### 4.4.1 <u>Case</u>

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed, preform-soldered or glass frit-sealed.

#### 4.4.2 Lead Material and Finish

For dual-in-line and flat packages, the material shall be either Type 'D' or Type 'G' with either Type '4' or Type '7' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. For chip carrier packages, the finish shall be either Type '4' or Type '7' in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

#### 4.5 MARKING

#### 4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

#### 4.5.2 <u>Lead Identification</u>

For dual-in-line and flat packages, an index shall be located at the top of the package in the position defined in Note 1 to Figure 2 or, alternatively, a tab may be used to identify Pin No. 1. The pin numbering must be read with the index or tab on the left-hand side. For chip carrier packages, the index shall be as defined by Figure 2(b).



PAGE 15

ISSUE 2

#### 4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

	<u>920501202B</u>	
Detail Specification Number		
Type Variant (see Table 1(a))		
Testing Level (Blor Clas applicable)		

#### 4.5.4 <u>Traceability Information</u>

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

#### 4.6 <u>ELECTRICAL MEASUREMENTS</u>

#### 4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.

#### 4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at  $T_{amb} = +125(+0-5)$  °C and -55(+5-0) °C respectively.

#### 4.6.3 Circuits for Electrical Measurements

Circuits for use in performing electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

#### 4.7 BURN-IN TESTS

#### 4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at  $T_{amb}$  = +22±3 °C. The parameter drift values ( $\Delta$ ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

#### 4.7.2 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for power burn-in shall be as specified in Table 5 of this specification.

#### 4.7.3 <u>Electrical Circuits for Power Burn-in</u>

Circuits for use in performing the power burn-in tests are shown in Figure 5 of this specification.



PAGE 16

ISSUE 2

## TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIMITS		UNIT
140.	OTATACTERIOTICS	MIL-STD FIG. D/F = DIP AND FP C = CCP)		MIN	МАХ	OIVII		
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	
2 to 7	Input Current High Level 1	l <sub>IH1</sub>	3010	4(a)	V <sub>CC</sub> = 5.5V, V <sub>IN</sub> = 2.7V (Pins D/F 1-2-3-4-5-6) (Pins C 2-3-4-5-7-8)	-	20	μΑ
8 to 13	Input Current High Level 2 (Max. Input Voltage)	I <sub>IH2</sub>	3010	4(a)	V <sub>CC</sub> = 5.5V, V <sub>IN</sub> = 7.0V (Pins D/F 1-2-3-4-5-6) (Pins C 2-3-4-5-7-8)	,	100	μΑ
14 to 19	Input Clamp Voltage	V <sub>IC</sub>	3008	4(b)	V <sub>CC</sub> = 4.5V, I <sub>IN</sub> = -18mA Note 2 (Pins D/F 1-2-3-4-5-6) (Pins C 2-3-4-5-7-8)	-	- 1.5	V
20 to 25	Input Current Low Level	l <sub>IL</sub>	3009	4(c)	V <sub>CC</sub> = 5.5V, V <sub>II.</sub> = 0.4V (Pins D F 1-2-3-4-5-6) (Pins C 2-3-4-5-7-8)	-	- 100	μΑ
26 to 33	Output Voltage Low Level	V <sub>OL</sub>	3007	4(d)	$V_{CC}$ = 4.5V, $V_{IH}$ = 2.0V $V_{IL}$ = 0.7V, $I_{OL}$ = 4.0mA (Pins D/F 7-9-10-11-12- 13-14-15) (Pins C 9-12-13-14-15-17- 18-19)		0.4	V
34 to 41	Output Voltage High Level 1	V <sub>OH1</sub>	3006	4(e)	$V_{CC}$ = 4.5V, $V_{IH}$ = 2.0V $V_{IL}$ = 0.7V, $I_{OH}$ = -400 $\mu$ A (Pins D/F 7-9-10-11-12-13-14-15) (Pins C 9-12-13-14-15-17-18-19)	2.5	-	V
42 to 49	Output Voltage High Level 2	V <sub>OH2</sub>	3006	4(e)	$V_{CC}$ = 5.5V, $V_{IH}$ = 2.0V $V_{IL}$ = 0.7V, $I_{OH}$ = -400 $\mu$ A (Pins D/F 7-9-10-11-12-13-14-15) (Pins C 9-12-13-14-15-17-18-19)	3.5	-	V



PAGE 17

ISSUE 2

#### TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIMITS		UNIT
NO.	OTIVITA OTENION	OTWIDOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	ONIT
50 to 57	One Half of the True Output Short Circuit Current	I <sub>OS/2</sub>	3011	4(f)	$V_{CC}$ = 5.5V, $V_{OUT}$ = 2.25V Note 3 (Pins D/F 7-9-10-11-12-13-14-15) (Pins C 9-12-13-14-15-17-18-19)	- 30	- 112	mA
58	Supply Current	lcc	3005	4(g)	V <sub>CC</sub> = 5.5V Note 4 (Pin D/F 16) (Pin C 20)	-	10	mA

#### **NOTES**

- 1. Go-no-go test with  $V_{IL} = 0.3V$ ,  $V_{IH} = 3.0V$ , trip point 1.5V.
- 2. All inputs and outputs not under test shall be open.
- 3. No more than 1 output should be tested at a time.
- 4. I<sub>CC</sub> is measured with G1 at 4.5V and all other inputs grounded.
- Propagation delay measurements shall be performed as a go-no-go test on a 100% basis.
   Read-and-record measurements shall be performed on an LTPD7 sample basis following the Chart III Burn-in Test.



PAGE 18

ISSUE 2

## TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD TEST		TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP	LIMITS		UNIT
NO.	CHATACTERISTICS	3 TWIBOL	MIL-STD 883	FIG.	C = CCP) (NOTE 5)	MIN	MAX	UNIT
59 to 106	Propagation Delay Low to High, from A or B or C to any Y	t <sub>PLH1</sub>	3003	4(h)	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	6.0	27	ns
107 to 154	Propagation Delay High to Low, from A or B or C to any Y	t <sub>PHL1</sub>	3003	4(h)	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	6.0	22	ns
155 to 202	Propagation Delay Low to High, from Enable to any Y	₹PLH2	3003	4(h)	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	4.0	20	ns
203 to 250	Propagation Delay High to Low, from Enable to any Y	<sup>†</sup> PHL2	3003	4(h)	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	5.0	20	ns



PAGE 19

ISSUE 2

## TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES, + 125(+0-5) °C AND - 55(+5-0) °C

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIMITS		UNIT
110.	OTATACTERIOTICS	STIVIDOL	MIL-STD 883	FIG.	FIG. D/F = DIP AND FP C = CCP)		MAX	OIVII
1	Functional Test	~	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 7	Input Current High Level 1	l <sub>IH1</sub>	3010	4(a)	$V_{CC}$ = 5.5V, $V_{IN}$ = 2.7V (Pins D:F 1-2-3-4-5-6) (Pins C 2-3-4-5-7-8)	-	20	μΑ
8 to 13	Input Current High Level 2 (Max. Input Voltage)	l <sub>IH2</sub>	3010	4(a)	$V_{CC}$ = 5.5V, $V_{IN}$ = 7.0V (Pins D/F 1-2-3-4-5-6) (Pins C 2-3-4-5-7-8)	-	100	μΑ
14 to 19	Input Clamp Voltage	V <sub>IC</sub>	3008	4(b)	$V_{CC}$ = 4.5V, $I_{IN}$ = - 18mA Note 2 (Pins D/F 1-2-3-4-5-6) (Pins C 2-3-4-5-7-8)	-	- 1.5	V
20 to 25	input Current Low Level	l <sub>IL</sub>	3009	4(c)	$V_{CC}$ = 5.5V, $V_{IL}$ = 0.4V (Pins D/F 1-2-3-4-5-6) (Pins C 2-3-4-5-7-8)	-	- 100	μΑ
26 to 33	Output Voltage Low Level	V <sub>OL</sub>	3007	4(d)	$V_{CC}$ = 4.5V, $V_{IH}$ = 2.0V $V_{IL}$ = 0.7V, $I_{OL}$ = 4.0mA (Pins D/F 7-9-10-11-12-13-14-15) (Pins C 9-12-13-14-15-17-18-19)	-	0.4	V
34 to 41	Output Voltage High Level 1	V <sub>OH1</sub>	3006	4(e)	$V_{CC}$ = 4.5V, $V_{IH}$ = 2.0V $V_{IL}$ = 0.7V, $I_{OH}$ = -400 $\mu$ A (Pins D/F 7-9-10-11-12-13-14-15) (Pins C 9-12-13-14-15-17-18-19)	2.5	-	V
42 to 49	Output Voltage High Level 2	V <sub>OH2</sub>	3006	4(e)	$V_{CC}$ = 5.5V, $V_{IH}$ = 2.0V $V_{IL}$ = 0.7V, $I_{OH}$ = -400 $\mu$ A (Pins D/F 7-9-10-11-12-13-14-15) (Pins C 9-12-13-14-15-17-18-19)	3.5	-	V



PAGE 20

ISSUE 2

#### TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES, + 125(+0-5) °C AND -55(+5-0) °C (CONT'D)

NO. CHARACTERISTICS		SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIMITS		UNIT
	CHAINOTENIONOS	STWIDOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	ONIT
50 to 57	One Half of the True Output Short Circuit Current	los/2	3011	4(f)	V <sub>CC</sub> = 5.5V, V <sub>OUT</sub> = 2.25V Note 3 (Pins D/F 7-9-10-11-12-13- 14-15) (Pins C 9-12-13-14-15-17- 18-19)	- 30	- 112	mA
58	Supply Current	lcc	3005	4(g)	V <sub>CC</sub> = 5.5V Note 4 (Pin D/F 16) (Pin C 20)	-	10	mA



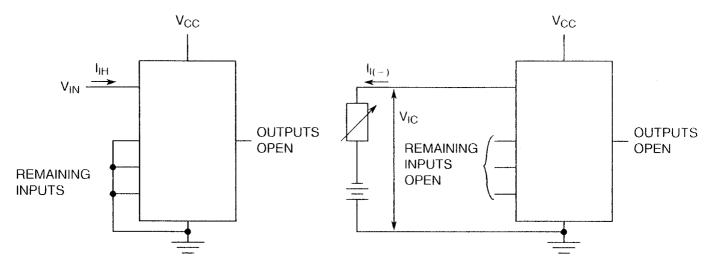
PAGE 21

ISSUE 2

#### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

#### FIGURE 4(a) - INPUT CURRENT HIGH LEVEL

#### FIGURE 4(b) - INPUT CLAMP VOLTAGE



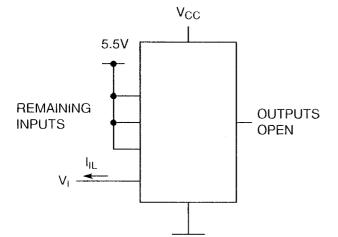
#### **NOTES**

1. Each input to be tested separately.

#### **NOTES**

1. Each input to be tested separately.

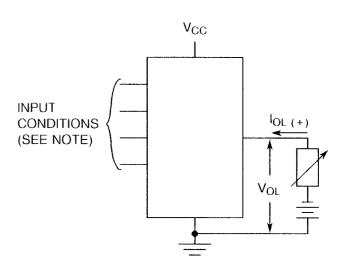
#### FIGURE 4(c) - LOW LEVEL INPUT CURRENT



#### **NOTES**

1. Each input to be tested separately.

#### FIGURE 4(d) - LOW LEVEL OUTPUT VOLTAGE



#### NOTES

1. Test per Truth Table



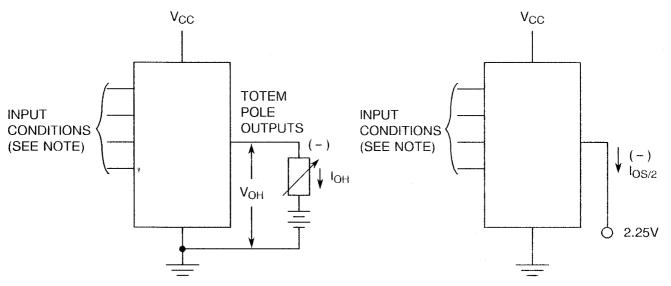
PAGE 22

ISSUE 2

#### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

#### FIGURE 4(e) - HIGH LEVEL OUTPUT VOLTAGE

## FIGURE 4(f) - ONE HALF SHORT CIRCUIT OUTPUT CURRENT



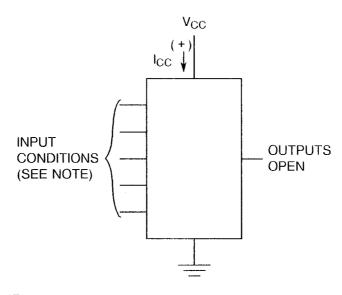
#### **NOTES**

1. Test per Truth Table.

#### **NOTES**

- 1. For Y measurement:  $\overline{G2} = 4.5V$  with all other Inputs Grounded.
- 2. No more than one output should be tested at a time.

#### FIGURE 4(g) - SUPPLY CURRENT



#### **NOTES**

1. See Note 4 on Page 17.

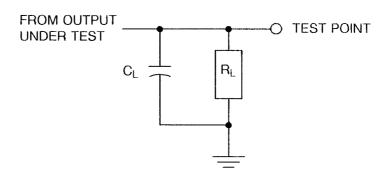


PAGE 23

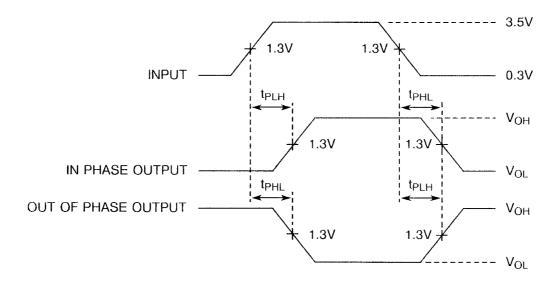
ISSUE 2

#### FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

#### FIGURE 4(h) - DYNAMIC TEST AND SWITCHING WAVEFORMS



#### **VOLTAGE WAVEFORMS - PROPAGATION DELAY TIMES**



#### **NOTES**

- 1. The generator has the following characteristics:  $t_f = t_f = 2$ ns, PRR = 1MHz,  $Z_{out} = 50\Omega$ , Duty Cycle = 50%.
- 2.  $C_L = 50pF \pm 5\%$  including scope probe, wiring and stray capacitance without package in test fixture.
- 3. Each line and output tested separately.
- 4.  $R_L = 500\Omega \pm 5\%$ .



PAGE 24

ISSUE 2

#### **TABLE 4 - PARAMETER DRIFT VALUES**

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
2 to 7	Input Current High Level 1	l <sub>IH1</sub>	As per Table 2	As per Table 2	±20 or (1) ±0.5	% μA
20 to 25	Input Current Low Level	I <sub>IL</sub>	As per Table 2	As per Table 2	± 10	μΑ
26 to 33	Output Voltage Low Level	V <sub>OL</sub>	As per Table 2	As per Table 2	± 60	mV
34 to 41	Output Voltage High Level 1	V <sub>OH1</sub>	As per Table 2	As per Table 2	± 200	mV
42 to 49	Output Voltage High Level 2	V <sub>OH2</sub>	As per Table 2	As per Table 2	± 200	mV

#### **NOTES**

1. Whichever is greater referred to the initial value.

TABLE 5 - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TEST

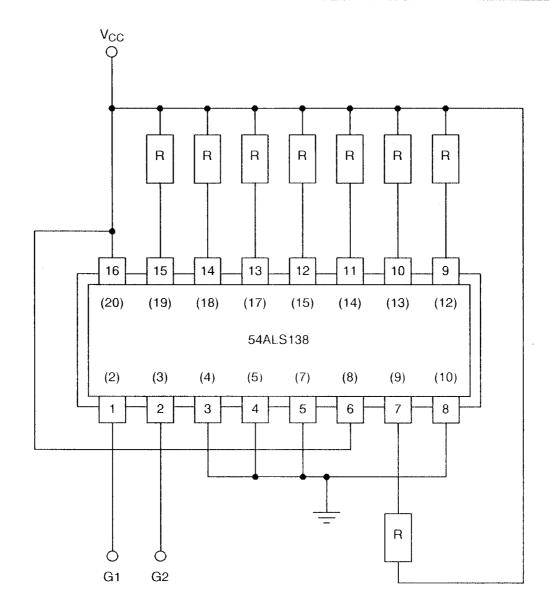
NO.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T <sub>amb</sub>	+ 125( + 0 - 5)	°C
2	Power Supply Voltage	$V_{\rm CC}$	+ 5( + 0.5 – 0)	V
3	Pulse Voltage	$V_{GEN}$	0.5 max. to 3.0 min.	Vac
4	Frequency	f G1 G2	100 50 (See Note 1)	Hz
5	Fan-out	-	10	-
6	Rise Time	t <sub>r</sub>	50 max.	μs
7	Fall Time	t <sub>f</sub>	50 max.	μs
8	Duty Cycle	-	20 min.	%

NOTES
1. Tolerance ± 10%.

PAGE 25

ISSUE 2

#### FIGURE 5 - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TEST



## **NOTES**

- 1. Pin numbers in parenthesis are for the chip carrier package.
- 2.  $R = 1.2k\Omega$ .



PAGE 26

ISSUE 2

## 4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC SPECIFICATION NO. 9000)</u>

#### 4.8.1 <u>Electrical Measurements on Completion of Environmental Tests</u>

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at  $T_{amb}$  = +22 ±3 °C.

#### 4.8.2 <u>Electrical Measurements at Intermediate Points during Endurance Tests</u>

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.

#### 4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.

#### 4.8.4 Conditions for Operating Life Tests

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

#### 4.8.5 <u>Electrical Circuits for Operating Life Tests</u>

Circuits for use in performing the operating life tests are shown in Figure 5.

#### 4.8.6 <u>Conditions for High Temperature Storage Test</u>

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The conditions for high temperature storage shall be  $T_{amb} = +150(+0-5)$  °C.



PAGE 27

ISSUE 2

## TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTS

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR	TEST	CHAN	UNIT	
INO.	NO. CHARACTERISTICS		TEST METHOD	CONDITIONS	(Δ)	ABSOLUTE	OMI
2 to 7	Input Current High Level 1	l <sub>IH1</sub>	As per Table 2	As per Table 2	<u>±</u> 1	-	μΑ
8 to 13	Input Current High Level 2 (Max. Input Voltage)	l <sub>IH2</sub>	As per Table 2	As per Table 2	-	100	μА
20 to 25	Input Current Low Level	I <sub>IL</sub>	As per Table 2	As per Table 2	± 10	-	μΑ
26 to 33	Output Voltage Low Level	V <sub>OL</sub>	As per Table 2	As per Table 2	± 60	-	mV
34 to 41	Output Voltage High Level 1	V <sub>OH1</sub>	As per Table 2	As per Table 2	± 200	_	mV
42 to 49	Output Voltage High Level 2	V <sub>OH2</sub>	As per Table 2	As per Table 2	±200	-	mV
58	Supply Current	lcc	As per Table 2	As per Table 2	± 20	-	%



PAGE 28

ISSUE 2

## APPENDIX 'A'

Page 1 of 1

## AGREED DEVIATIONS FOR TEXAS INSTRUMENTS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS						
Para. 4.2.1	Scanning Electron Microscope (SEM) Inspection may be performed TIF document TIF 3.61.610.001.						
Para. 4.2.2	Prior to Die Shear Test TIF may perform a Radiographic Inspection on the randomly chosen samples to be subjected to this test, using TIF document TI 150.42-3002.						
Para. 4.2.3	Radiographic Inspection may be performed using TIF document TI 50.42-3002.						